

TMUX6104 36V、低容量、低リーク電流、 高精度の4:1アナログ・マルチプレクサ

1 特長

- 低いオン容量: 5pF
- 低入力リーク電流: 5pA
- 低電荷注入: 0.35pC
- レール・ツー・レール動作
- 広い電源電圧範囲: $\pm 5V \sim \pm 16.5V$ (デュアル電源)、または $10V \sim 16.5V$ (シングル電源)
- 低オン抵抗: 125 Ω
- 遷移時間: 88ns
- Break-Before-Makeの切り替え動作
- V_{DD} に接続可能なENピン、プルダウン内蔵
- ロジック・レベル: $2V \sim V_{DD}$
- 低い消費電流: 17 μA
- ESD保護(HBM): 2000V
- 業界標準のTSSOPパッケージ

2 アプリケーション

- ファクトリ・オートメーションと産業プロセス制御
- プログラマブル・ロジック・コントローラ (PLC)
- アナログ入力モジュール
- ATE試験装置
- デジタル・マルチメータ
- バッテリー・モニタリング・システム

3 概要

TMUX6104は新型の相補型金属酸化膜半導体(CMOS)アナログ・マルチプレクサ(MUX)で、4:1のシングルエンド多重化を行います。これらのデバイスはデュアル電源($\pm 5V \sim \pm 16.5V$)、シングル電源($10V \sim 16.5V$)、または非対称電源($V_{DD} = 12V$ 、 $V_{SS} = -5V$ など)で適切に動作します。すべてのデジタル入力はスレッシュホールドがTTL (Transistor-Transistor Logic)互換で、TTLおよびCMOS両方のロジックとの互換性が保証されています。

TMUX6104は、アドレス・ピン(A0/A1)とイネーブル・ピン(EN)のステータスに従い、4つの入力の1つ(Sx)を共通の出力(D)に多重化します。各スイッチはオン位置において、どちらの方向にも同程度に伝導性が高く、電源電圧までの入力信号範囲をサポートします。オフ状態では、電源電圧までの信号レベルがブロックされます。すべてのスイッチは、Break-Before-Make (BBM)スイッチング動作を行います。

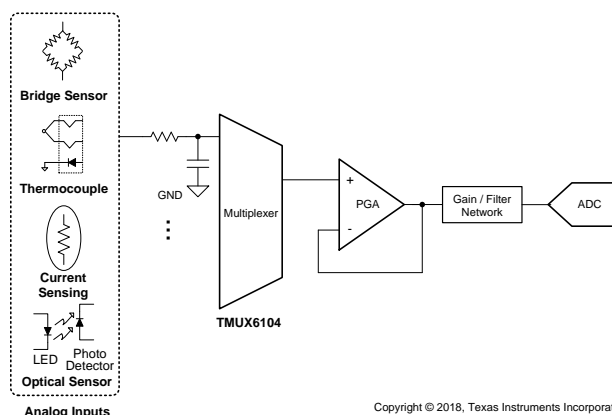
TMUX6104デバイスは、テキサス・インスツルメンツの高精度スイッチおよびマルチプレクサ・ファミリの製品です。このファミリのデバイスはリーク電流と電荷注入が非常に小さいため、高精度の測定アプリケーションに使用可能です。消費電流が17 μA と低いため、携帯型アプリケーションにも使用できます。

製品情報⁽¹⁾

型番	パッケージ	本体サイズ(公称)
TMUX6104	TSSOP (14)	5.00mm×4.40mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にあるパッケージ・オプションについての付録を参照してください。

概略回路図



Copyright © 2018, Texas Instruments Incorporated



目次

1	特長	1	8.2	Functional Block Diagram	18
2	アプリケーション	1	8.3	Feature Description	18
3	概要	1	8.4	Device Functional Modes	20
4	改訂履歴	2	9	Application and Implementation	21
5	Pin Configuration and Functions	3	9.1	Application Information	21
6	Specifications	4	9.2	Typical Application	21
6.1	Absolute Maximum Ratings	4	10	Power Supply Recommendations	23
6.2	ESD Ratings	4	11	Layout	24
6.3	Thermal Information	4	11.1	Layout Guidelines	24
6.4	Recommended Operating Conditions	4	11.2	Layout Example	24
6.5	Electrical Characteristics (Dual Supplies: ± 15 V)	5	12	デバイスおよびドキュメントのサポート	25
6.6	Switching Characteristics (Dual Supplies: ± 15 V)	6	12.1	ドキュメントのサポート	25
6.7	Electrical Characteristics (Single Supply: 12 V)	6	12.2	ドキュメントの更新通知を受け取る方法	25
6.8	Switching Characteristics (Single Supply: 12 V)	7	12.3	コミュニティ・リソース	25
6.9	Typical Characteristics	9	12.4	商標	25
7	Parameter Measurement Information	11	12.5	静電気放電に関する注意事項	25
7.1	Truth Table	11	12.6	Glossary	25
8	Detailed Description	12	13	メカニカル、パッケージ、および注文情報	25
8.1	Overview	12			

4 改訂履歴

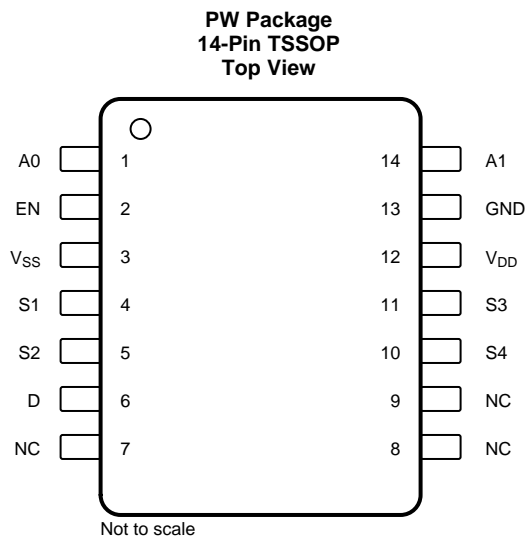
資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

2018年2月発行のものから更新

Page

• デバイスのステータスを「事前情報」から「量産データ」に変更	1
---------------------------------------	---

5 Pin Configuration and Functions



Pin Functions

PIN		TYPE	DESCRIPTION
NAME	NO.		
A0	1	I	Address line 0
A1	14	I	Address line 1
D	6	I/O	Drain pin. Can be an input or output.
EN	2	I	Active high digital input. When this pin is low, all switches are turned off. When this pin is high, the A0 and A1 logic inputs determine which switch is turned on.
GND	13	P	Ground (0 V) reference
NC	7, 8, 9	No Connect	No internal connection
S1	4	I/O	Source pin 1. Can be an input or output.
S2	5	I/O	Source pin 2. Can be an input or output.
S3	11	I/O	Source pin 3. Can be an input or output.
S4	10	I/O	Source pin 4. Can be an input or output.
V _{DD}	12	P	Positive power supply. This pin is the most positive power-supply potential. For reliable operation, connect a decoupling capacitor ranging from 0.1 μ F to 10 μ F between V _{DD} and GND.
V _{SS}	3	P	Negative power supply. This pin is the most negative power-supply potential. In single-supply applications, this pin can be connected to ground. For reliable operation, connect a decoupling capacitor ranging from 0.1 μ F to 10 μ F between V _{SS} and GND.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{DD} to V _{SS}	Supply voltage		36	V
V _{DD} to GND		-0.3	18	V
V _{SS} to GND		-18	0.3	V
V _{DIG}	Digital input pin (EN, A0, A1) voltage	GND -0.3	V _{DD} +0.3	V
I _{DIG}	Digital input pin (EN, A0, A1) current	-30	30	mA
V _{ANA_IN}	Analog input pin (Sx) voltage	V _{SS} -0.3	V _{DD} +0.3	V
I _{ANA_IN}	Analog input pin (Sx) current	-30	30	mA
V _{ANA_OUT}	Analog output pin (D) voltage	V _{SS} -0.3	V _{DD} +0.3	V
I _{ANA_OUT}	Analog output pin (D) current	-30	30	mA
T _A	Ambient temperature	-55	125	°C
T _J	Junction temperature		150	°C
T _{stg}	Storage temperature	-65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Thermal Information

THERMAL METRIC ⁽¹⁾		TMUX6104	UNIT
		PW (TSSOP)	
		14 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	122.4	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	52.0	°C/W
R _{θJB}	Junction-to-board thermal resistance	65.4	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	8.1	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	64.8	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{DD} to V _{SS} ⁽¹⁾	Power supply voltage differential	10		33	V
V _{DD} to GND	Positive power supply voltage (single supply, V _{SS} = 0 V)	10		16.5	V
V _{DD} to GND	Positive power supply voltage (dual supply)	5		16.5	V
V _{SS} to GND	Negative power supply voltage (dual supply)	-5		-16.5	V

(1) V_{DD} and V_{SS} can be any value as long as 10 V ≤ (V_{DD} - V_{SS}) ≤ 33 V.

Recommended Operating Conditions (continued)

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_S ⁽²⁾	Source pins voltage	V_{SS}		V_{DD}	V
V_D	Drain pin voltage	V_{SS}		V_{DD}	V
V_{DIG}	Digital input pin (EN, A0, A1) voltage	0		V_{DD}	V
I_{CH}	Channel current ($T_A = 25^\circ\text{C}$)	-25		25	mA
T_A	Ambient temperature	-40		125	$^\circ\text{C}$

(2) V_S is the voltage on all the S pins.

6.5 Electrical Characteristics (Dual Supplies: $\pm 15\text{ V}$)

at $T_A = 25^\circ\text{C}$, $V_{DD} = 15\text{ V}$, and $V_{SS} = -15\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT	
ANALOG SWITCH								
V_A	Analog signal range		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	V_{SS}		V_{DD}	V	
R_{ON}	On-resistance	$V_S = 0\text{ V}$, $I_S = 1\text{ mA}$			125	170	Ω	
					145	200	Ω	
		$V_S = \pm 10\text{ V}$, $I_S = 1\text{ mA}$	$T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$		230	Ω		
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		250	Ω		
ΔR_{ON}	On-resistance mismatch between channels	$V_S = \pm 10\text{ V}$, $I_S = 1\text{ mA}$		1.5	6	Ω		
R_{ON_FLAT}	On-resistance flatness	$V_S = -10\text{ V}$, 0 V , $+10\text{ V}$, $I_S = 1\text{ mA}$	$T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$		26	45	Ω	
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$			53	Ω	
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$			58	Ω	
R_{ON_DRIFT}	On-resistance drift	$V_S = 0\text{ V}$			0.5		$\Omega/^\circ\text{C}$	
$I_{S(OFF)}$	Source off leakage current ⁽¹⁾	Switch state is off, $V_S = +10\text{ V}/-10\text{ V}$, $V_D = -10\text{ V}/+10\text{ V}$		-0.02	0.005	0.02	nA	
			$T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$		-0.13		0.05	nA
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		-1		0.5	nA
$I_{D(OFF)}$	Drain off leakage current ⁽¹⁾	Switch state is off, $V_S = +10\text{ V}/-10\text{ V}$, $V_D = -10\text{ V}/+10\text{ V}$		-0.05	0.01	0.05	nA	
			$T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$		-0.14		0.1	nA
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		-1		0.5	nA
$I_{D(ON)}$	Drain on leakage current	Switch state is on, $V_S = +10\text{ V}/-10\text{ V}$, $V_D = -10\text{ V}/+10\text{ V}$		-0.07	0.01	0.07	nA	
			$T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$		-0.27		0.15	nA
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		-2		1	nA
DIGITAL INPUT (EN, Ax pins)								
V_{IH}	Logic voltage high		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	2			V	
V_{IL}	Logic voltage low		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$			0.8	V	
$R_{PD(EN)}$	Pull-down resistance on EN pin				6		M Ω	
POWER SUPPLY								
I_{DD}	V_{DD} supply current	$V_A = 0\text{ V}$ or 3.3 V , $V_S = 0\text{ V}$, $V_{EN} = 3.3\text{ V}$	$T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$		17	24	μA	
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$			25	μA	
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$			27	μA	
I_{SS}	V_{SS} supply current	$V_A = 0\text{ V}$ or 3.3 V , $V_S = 0\text{ V}$, $V_{EN} = 3.3\text{ V}$			7	12	μA	
			$T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$			13	μA	
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$			15	μA	

(1) When V_S is positive, V_D is negative, and vice versa.

6.6 Switching Characteristics (Dual Supplies: ±15 V)

 at $T_A = 25^\circ\text{C}$, $V_{DD} = 15\text{ V}$, and $V_{SS} = -15\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{ON}	Enable turn-on time	$V_S = \pm 10\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$		85	120	ns
		$V_S = \pm 10\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$, $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$			130	ns
		$V_S = \pm 10\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$			140	ns
t_{OFF}	Enable turn-off time	$V_S = \pm 10\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$		53	65	ns
		$V_S = \pm 10\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$, $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$			70	ns
		$V_S = \pm 10\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$			75	ns
t_{TRAN}	Transition time	$V_S = 10\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$		88	125	ns
		$V_S = 10\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$, $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$			135	ns
		$V_S = 10\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$			145	ns
t_{BBM}	Break-before-make time delay	$V_S = 10\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	30	50		ns
Q_J	Charge injection	$V_S = 0\text{ V}$, $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$		-0.35		pC
		$V_S = -15\text{ V}$ to 15 V , $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$		-0.41		pC
O_{ISO}	Off-isolation	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$		-86		dB
X_{TALK}	Channel-to-channel crosstalk	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$, non-adjacent channels		-105		dB
		$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$, adjacent channels		-87		dB
I_L	Insertion loss	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$		-7		dB
ACPSRR	AC Power Supply Rejection Ratio	$R_L = 10\text{ k}\Omega$, $C_L = 5\text{ pF}$, $V_{PP} = 0.62\text{ V}$ on V_{DD} , $f = 1\text{ MHz}$		-52		dB
		$R_L = 10\text{ k}\Omega$, $C_L = 5\text{ pF}$, $V_{PP} = 0.62\text{ V}$ on V_{SS} , $f = 1\text{ MHz}$		-49		dB
BW	-3dB Bandwidth	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$		500		MHz
THD + N	Total harmonic distortion + noise	$R_L = 10\text{ k}\Omega$, $C_L = 5\text{ pF}$, $f = 20\text{ Hz}$ to 20 kHz		0.08		%
C_{IN}	Digital input capacitance	$V_{IN} = 0\text{ V}$ or V_{DD}		1.2		pF
$C_{S(OFF)}$	Source off-capacitance	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$		1.6	2.3	pF
$C_{D(OFF)}$	Drain off-capacitance	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$		3.8	4.2	pF
$C_{S(ON)}$, $C_{D(ON)}$	Source and drain on-capacitance	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$		5.0	6.5	pF

6.7 Electrical Characteristics (Single Supply: 12 V)

 at $T_A = 25^\circ\text{C}$, $V_{DD} = 12\text{ V}$, and $V_{SS} = 0\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
ANALOG SWITCH							
V_A	Analog signal range	$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	V_{SS}		V_{DD}	V
R_{ON}	On-resistance	$V_S = 10\text{ V}$, $I_S = 1\text{ mA}$			235	345	Ω
			$T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$			400	Ω
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$			440	Ω
ΔR_{ON}	On-resistance mismatch between channels	$V_S = 10\text{ V}$, $I_S = 1\text{ mA}$			2.4	12	Ω
			$T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$			19	Ω
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$			23	Ω
R_{ON_DRIFT}	On-resistance drift	$V_S = 0\text{ V}$			0.47		%/ $^\circ\text{C}$

Electrical Characteristics (Single Supply: 12 V) (continued)

at $T_A = 25^\circ\text{C}$, $V_{DD} = 12\text{ V}$, and $V_{SS} = 0\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$I_{S(OFF)}$	Source off leakage current ⁽¹⁾	Switch state is off, $V_S = 10\text{ V}/1\text{ V}$, $V_D = 1\text{ V}/10\text{ V}$		-0.02	0.005	0.02	nA
			$T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$	-0.1		0.05	nA
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	-0.8		0.4	nA
$I_{D(OFF)}$	Drain off leakage current ⁽¹⁾	Switch state is off, $V_S = 10\text{ V}/1\text{ V}$, $V_D = 1\text{ V}/10\text{ V}$		-0.03	0.01	0.03	nA
			$T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$	-0.1		0.08	nA
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	-0.8		0.4	nA
$I_{D(ON)}$	Drain on leakage current	Switch state is on, $V_S =$ floating, $V_D = 1\text{ V}/10\text{ V}$		-0.05	0.01	0.05	nA
			$T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$	-0.2		0.15	nA
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	-1.6		0.8	nA
DIGITAL INPUT (EN, Ax pins)							
V_{IH}	Logic voltage high		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	2			V
V_{IL}	Logic voltage low		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$			0.8	V
$R_{PD(EN)}$	Pull-down resistance on EN pin				6		M Ω
POWER SUPPLY							
I_{DD}	V_{DD} supply current	$V_A = 0\text{ V}$ or 3.3 V , $V_S = 0\text{ V}$, $V_{EN} = 3.3\text{ V}$			12	18	μA
			$T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$			19	μA
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$			21	μA

(1) When V_S is positive, V_D is negative, and vice versa.

6.8 Switching Characteristics (Single Supply: 12 V)

at $T_A = 25^\circ\text{C}$, $V_{DD} = 12\text{ V}$, and $V_{SS} = 0\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t_{ON}	Enable turn-on time	$V_S = 8\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$			91	125	ns
		$V_S = 8\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$, $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$				135	ns
		$V_S = 8\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$				145	ns
t_{OFF}	Enable turn-off time	$V_S = 8\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$			52	60	ns
		$V_S = 8\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$, $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$				70	ns
		$V_S = 8\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$				77	ns
t_{TRAN}	Transition time	$V_S = 8\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$			94	127	ns
		$V_S = 8\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$, $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$				140	ns
		$V_S = 8\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$				150	ns
t_{BBM}	Break-before-make time delay	$V_S = 8\text{ V}$, $R_L = 300\ \Omega$, $C_L = 35\text{ pF}$, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		30	55		ns
Q_J	Charge injection	$V_S = 6\text{ V}$, $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$			-0.2		pC
		$V_S = 0\text{ V}$ to 12 V , $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$			-0.2		pC
O_{ISO}	Off-isolation	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$			-86		dB
X_{TALK}	Channel-to-channel crosstalk	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$, non-adjacent channels			-107		dB
		$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$, adjacent channels			-87		dB
I_L	Insertion loss	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$			-14		dB
ACPSRR	AC Power Supply Rejection Ratio	$R_L = 10\text{ k}\Omega$, $C_L = 5\text{ pF}$, $V_{PP} = 0.62\text{ V}$, $f = 1\text{ MHz}$			-51		dB
BW	-3dB Bandwidth	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$			400		MHz

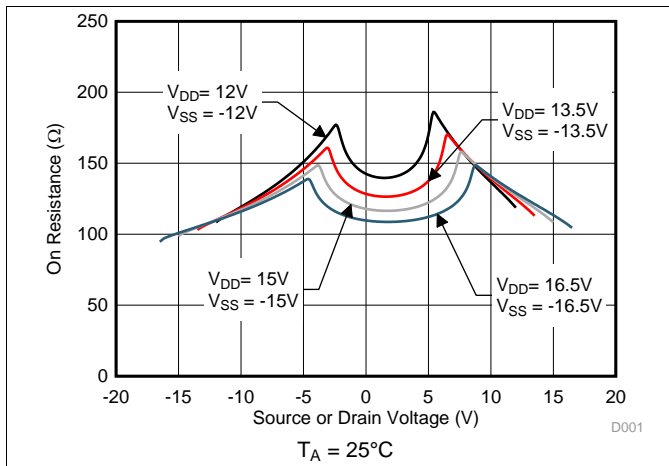
Switching Characteristics (Single Supply: 12 V) (continued)

 at $T_A = 25^\circ\text{C}$, $V_{DD} = 12\text{ V}$, and $V_{SS} = 0\text{ V}$ (unless otherwise noted)

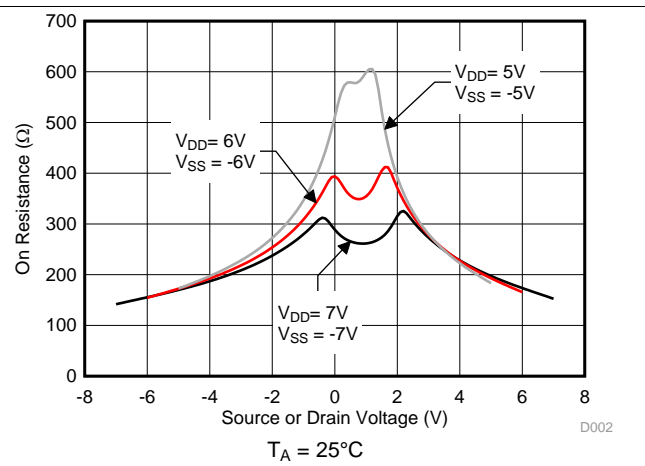
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
C_{IN}	Digital input capacitance	$V_{IN} = 0\text{ V}$ or V_{DD}		1.2		pF
$C_{S(OFF)}$	Source off-capacitance	$V_S = 6\text{ V}$, $f = 1\text{ MHz}$		1.9	2.3	pF
$C_{D(OFF)}$	Drain off-capacitance	$V_S = 6\text{ V}$, $f = 1\text{ MHz}$		4.6	5.3	pF
$C_{S(ON)}$, $C_{D(ON)}$	Source and drain on-capacitance	$V_S = 6\text{ V}$, $f = 1\text{ MHz}$		6.3	7.5	pF

6.9 Typical Characteristics

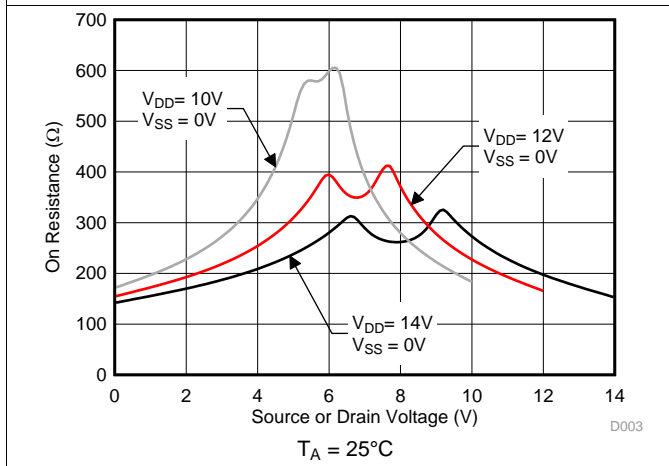
at $T_A = 25^\circ\text{C}$, $V_{DD} = 15\text{ V}$, and $V_{SS} = -15\text{ V}$ (unless otherwise noted)



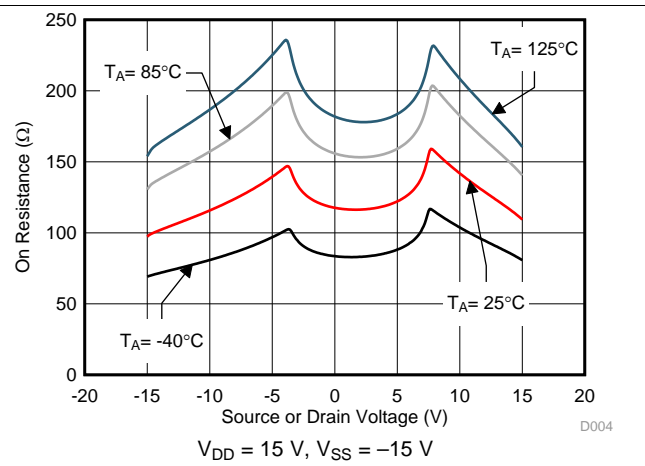
☒ 1. On-Resistance vs Source or Drain Voltage



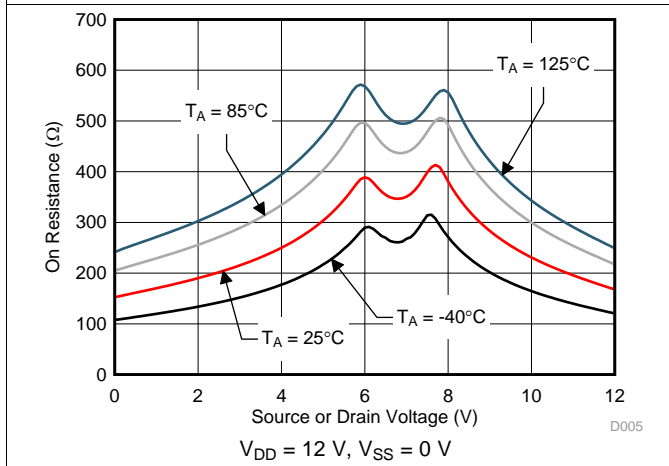
☒ 2. On-Resistance vs Source or Drain Voltage



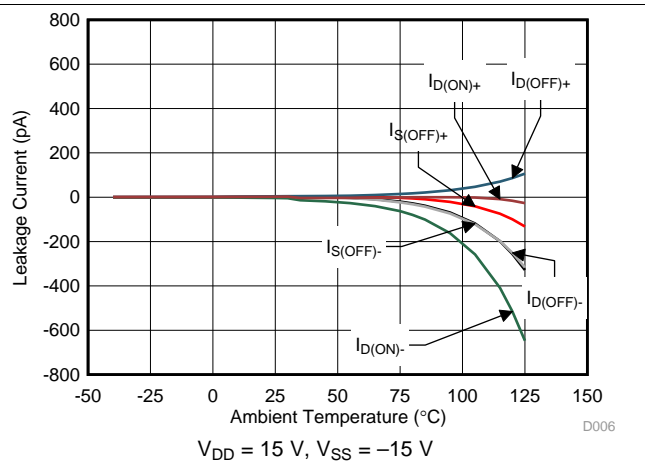
☒ 3. On-Resistance vs Source or Drain Voltage



☒ 4. On-Resistance vs Source or Drain Voltage



☒ 5. On-Resistance vs Source or Drain Voltage



☒ 6. Leakage Current vs Temperature

Typical Characteristics (continued)

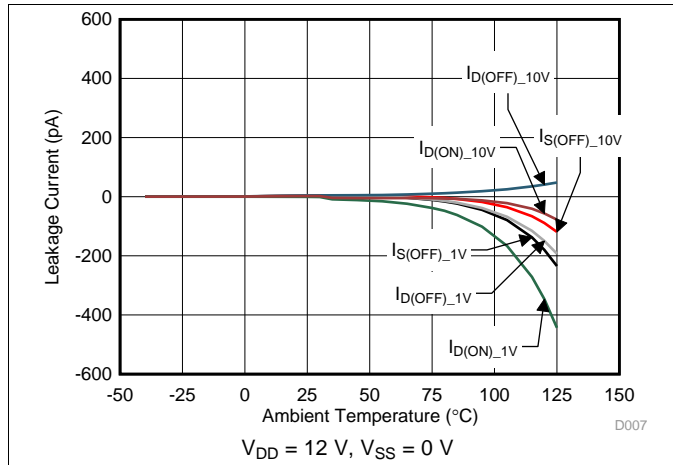


Figure 7. Leakage Current vs Temperature

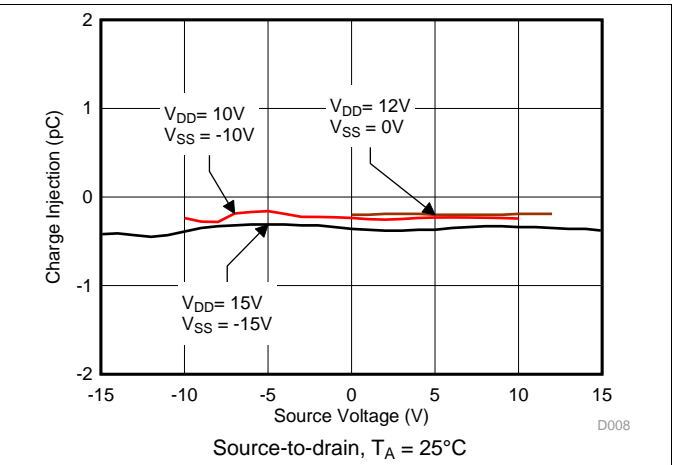


Figure 8. Charge Injection vs Source Voltage

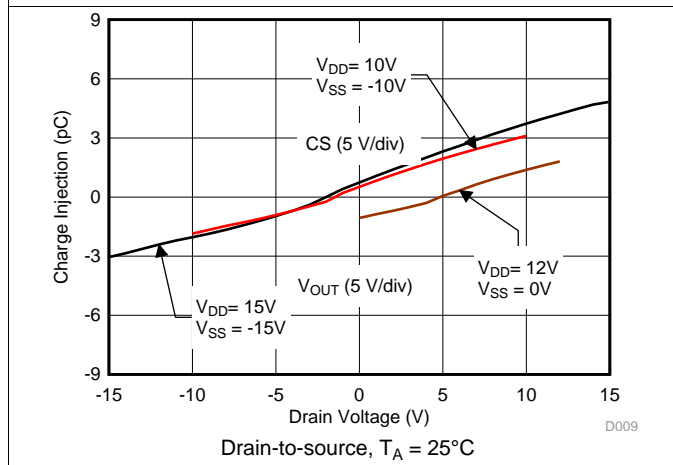


Figure 9. Charge Injection vs Drain Voltage

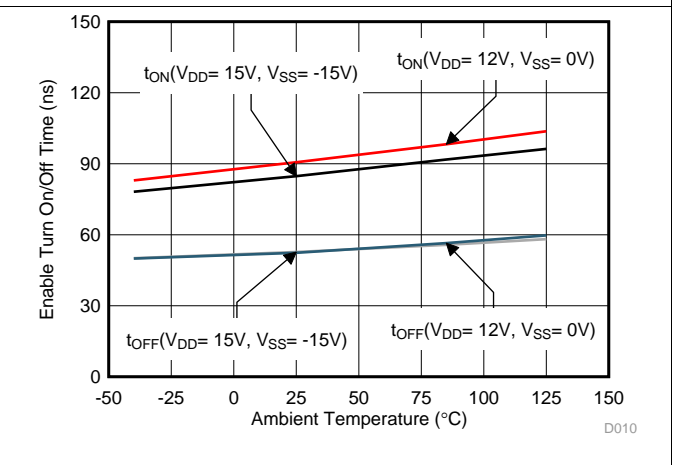


Figure 10. Turn-On and Turn-Off Times vs Temperature

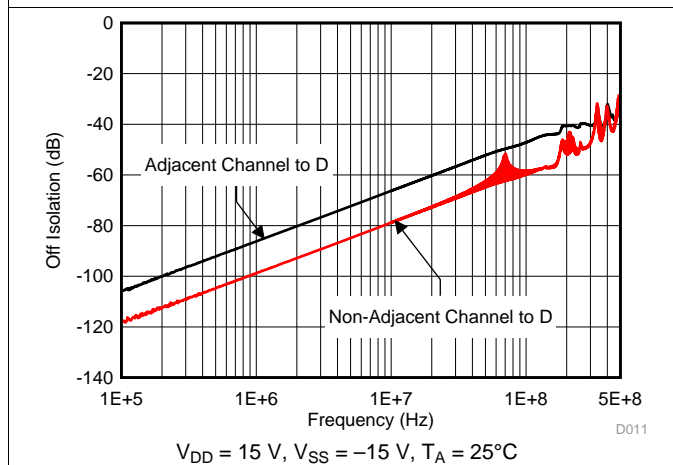


Figure 11. Off Isolation vs Frequency

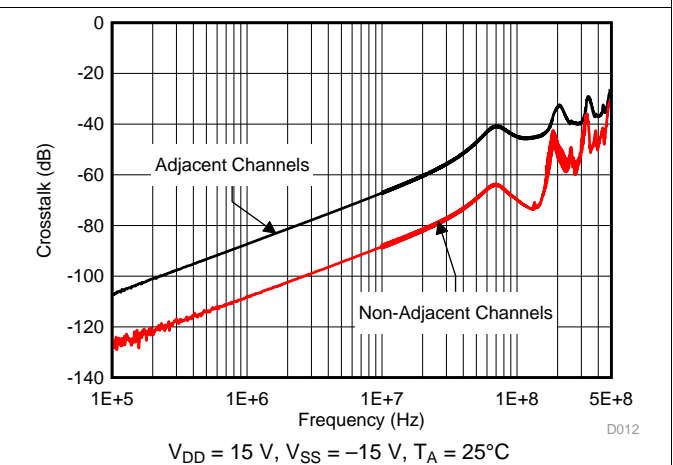


Figure 12. Crosstalk vs Frequency

Typical Characteristics (continued)

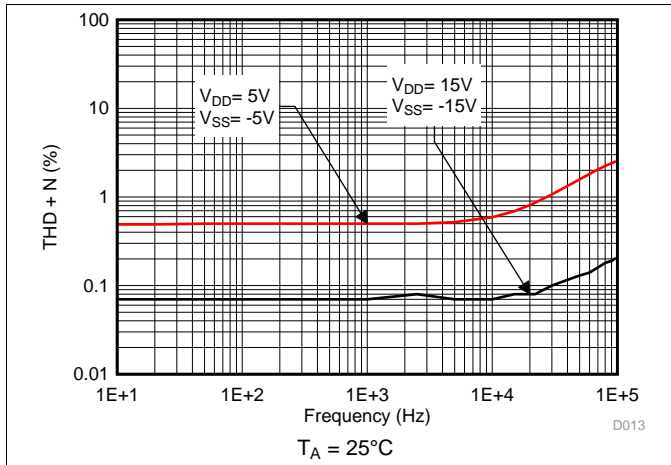


图 13. THD+N vs Frequency

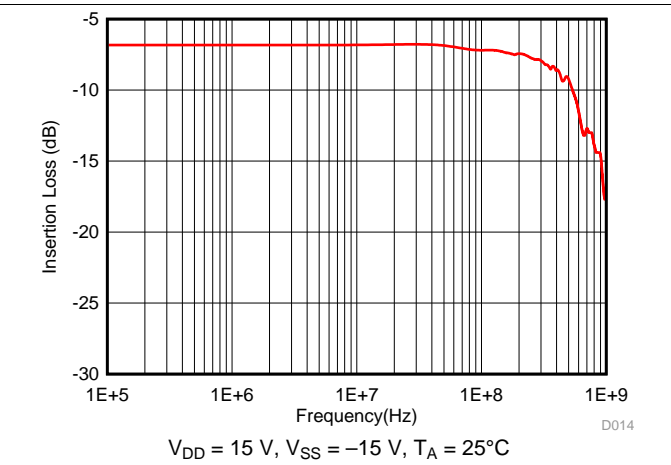


图 14. On Response vs. Frequency

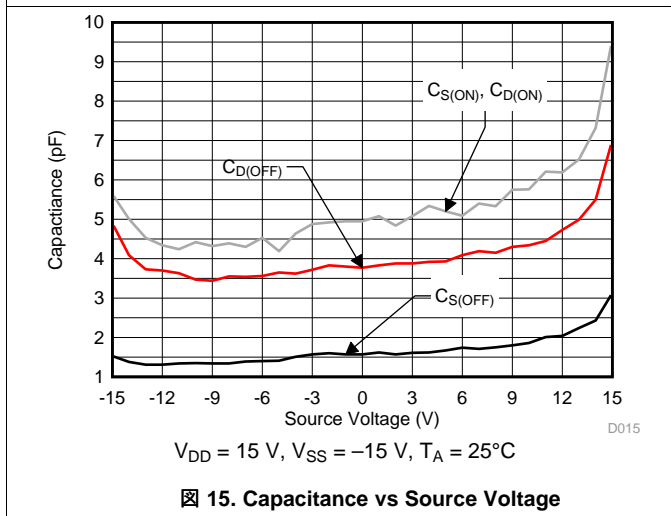


图 15. Capacitance vs Source Voltage

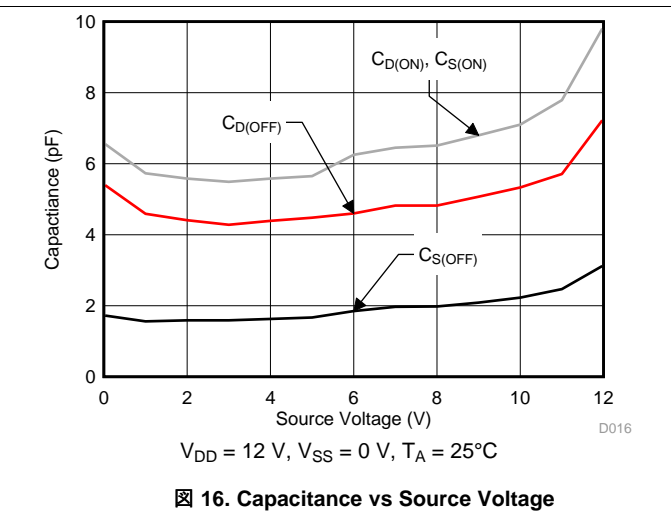


图 16. Capacitance vs Source Voltage

7 Parameter Measurement Information

7.1 Truth Table

表 1. TMUX6104 Truth Table

EN	A1	A0	STATE
0	X ⁽¹⁾	X ⁽¹⁾	All channels are off
1	0	0	Channel 1
1	0	1	Channel 2
1	1	0	Channel 3
1	1	1	Channel 4

(1) X denotes don't care..

8 Detailed Description

8.1 Overview

8.1.1 On-Resistance

The on-resistance of the TMUX6104 is the ohmic resistance across the source (Sx) and drain (D) pins of the device. The on-resistance varies with input voltage and supply voltage. The symbol R_{ON} is used to denote on-resistance. The measurement setup used to measure R_{ON} is shown in [Figure 17](#). Voltage (V) and current (I_{CH}) are measured using this setup, and R_{ON} is computed as shown in [Equation 1](#):

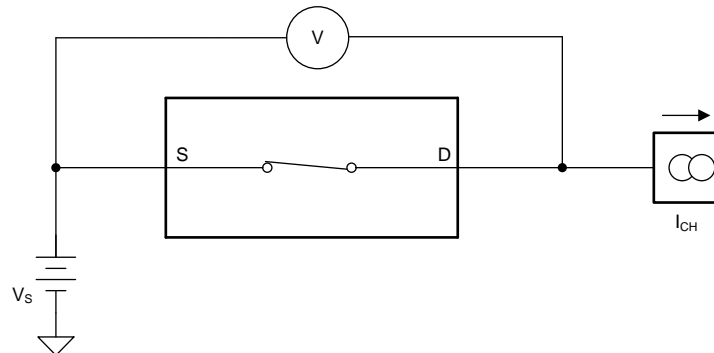


Figure 17. On-Resistance Measurement Setup

$$R_{ON} = V / I_{CH} \quad (1)$$

8.1.2 Off-Leakage Current

There are two types of leakage currents associated with a switch during the off state:

1. Source off-leakage current
2. Drain off-leakage current

Source leakage current is defined as the leakage current flowing into or out of the source pin when the switch is off. This current is denoted by the symbol $I_{S(OFF)}$.

Drain leakage current is defined as the leakage current flowing into or out of the drain pin when the switch is off. This current is denoted by the symbol $I_{D(OFF)}$.

The setup used to measure both off-leakage currents is shown in [Figure 18](#).

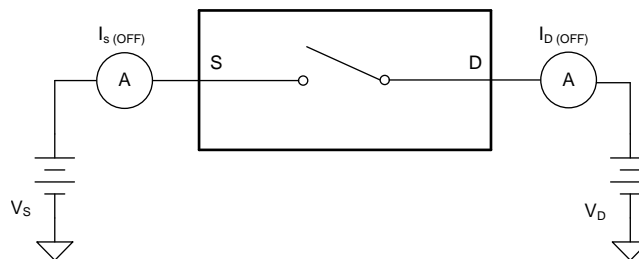
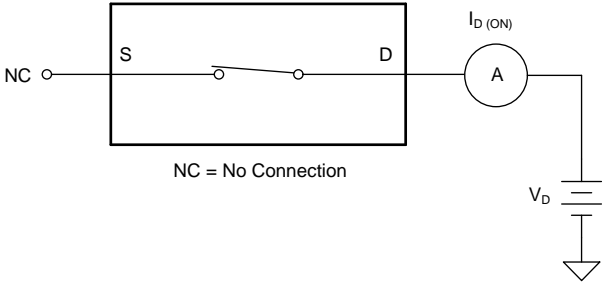
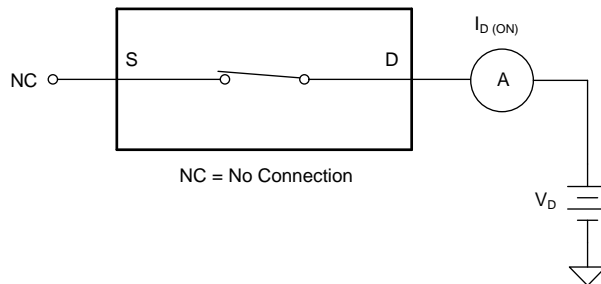


Figure 18. Off-Leakage Measurement Setup

Overview (continued)

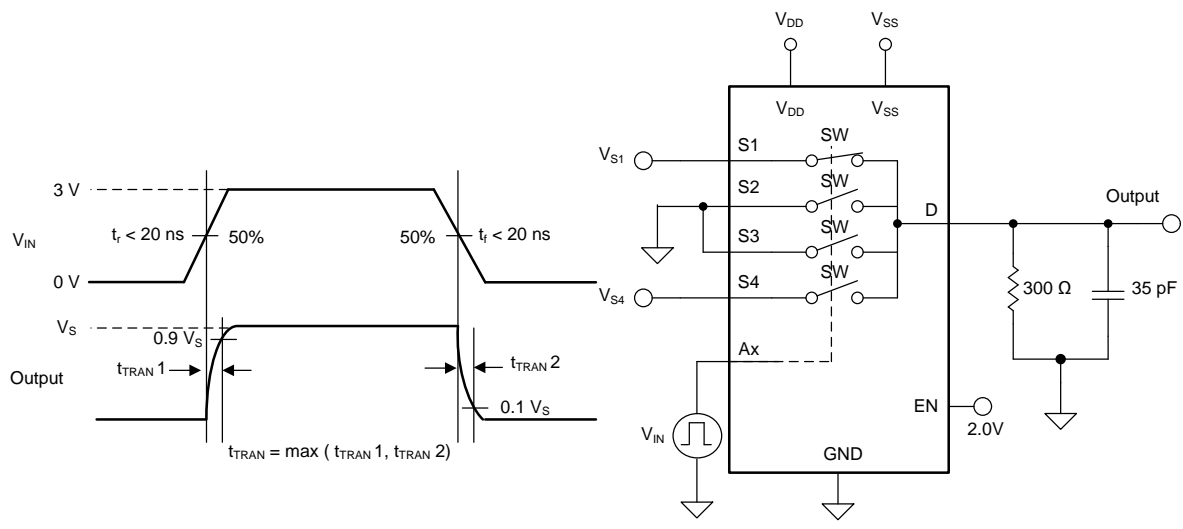
8.1.3 On-Leakage Current

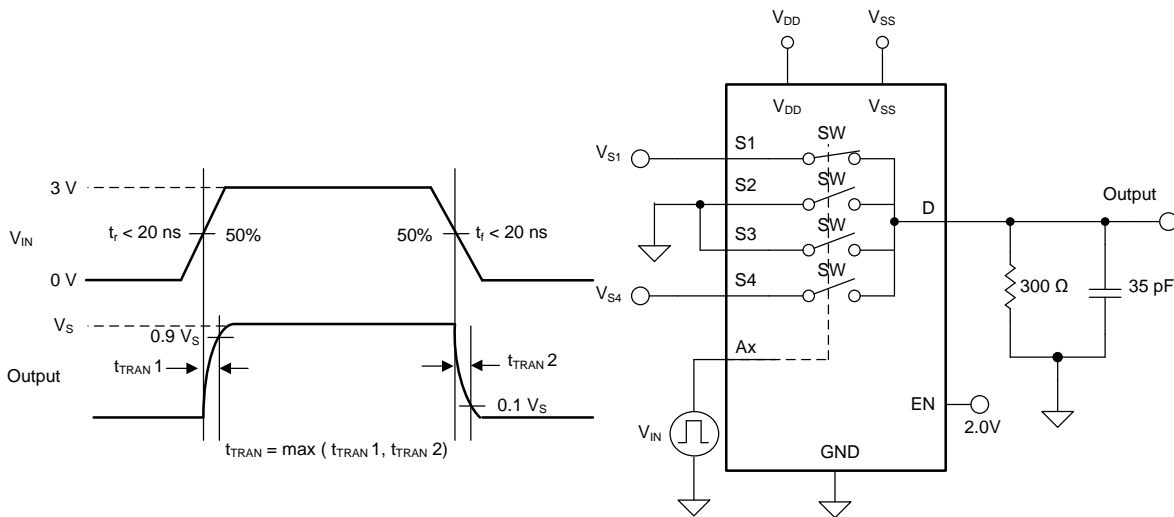
On-leakage current is defined as the leakage current that flows into or out of the drain pin when the switch is in the on state. The source pin is left floating during the measurement.  19 shows the circuit used for measuring the on-leakage current, denoted by $I_{D(ON)}$.



 19. On-Leakage Measurement Setup

8.1.4 Transition Time

Transition time is defined as the time taken by the output of the TMUX6104 to rise (to 90% of the transition) or fall (to 10% of the transition) after the digital address signal has fallen or risen to 50% of the transition.  20 shows the setup used to measure transition time, denoted by the symbol t_{TRAN} .



 20. Transition-Time Measurement Setup

Overview (continued)

8.1.5 Break-Before-Make Delay

Break-before-make delay is a safety feature that prevents two inputs from connecting when the TMUX6104 is switching. The TMUX6104 output first breaks from the on-state switch before making the connection with the next on-state switch. The time delay between the *break* and the *make* is known as break-before-make delay. [Figure 21](#) shows the setup used to measure break-before-make delay, denoted by the symbol t_{BBM} .

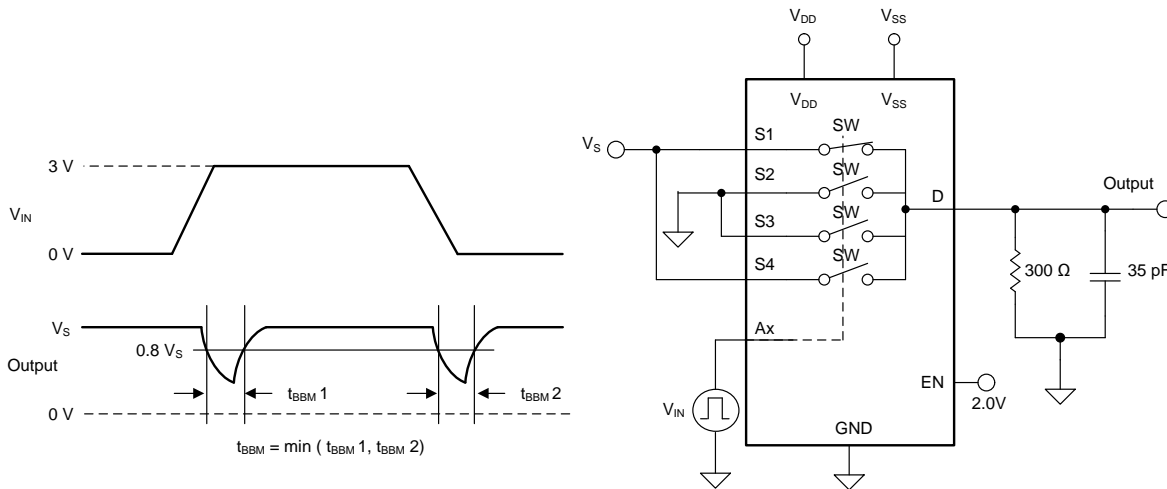


Figure 21. Break-Before-Make Delay Measurement Setup

8.1.6 Turn-On and Turn-Off Time

Turn-on time is defined as the time taken by the output of the TMUX6104 to rise to a 90% final value after the enable signal has risen to a 50% final value. [Figure 22](#) shows the setup used to measure turn-on time. Turn-on time is denoted by the symbol $t_{ON(EN)}$.

Turn off time is defined as the time taken by the output of the TMUX6104 to fall to a 10% initial value after the enable signal has fallen to a 50% initial value. [Figure 22](#) shows the setup used to measure turn-off time. Turn-off time is denoted by the symbol $t_{OFF(EN)}$.

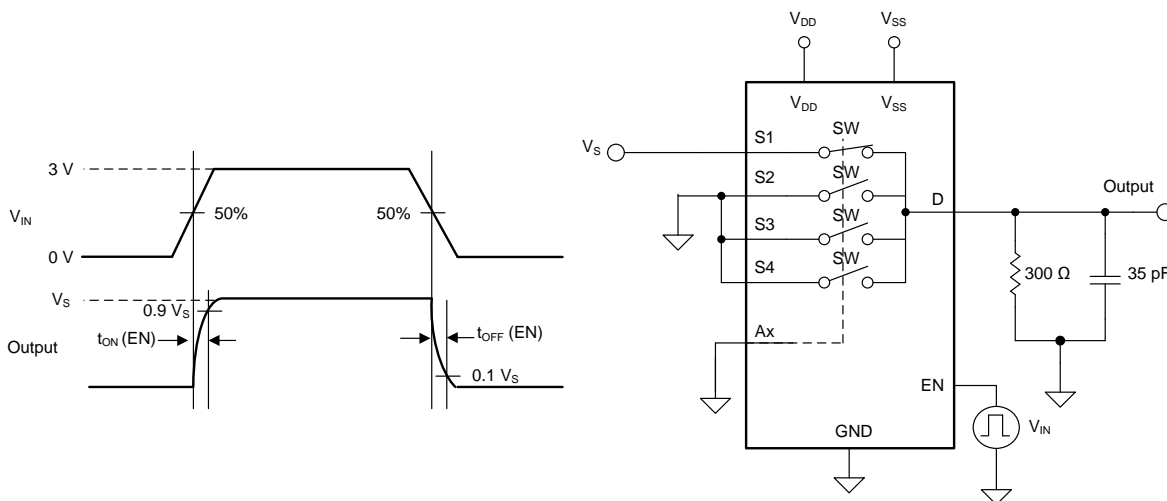


Figure 22. Turn-On and Turn-Off Time Measurement Setup

Overview (continued)

8.1.7 Charge Injection

The TMUX6104 have a simple transmission-gate topology. Any mismatch in capacitance between the NMOS and PMOS transistors results in a charge injected into the drain or source during the falling or rising edge of the gate signal. The amount of charge injected into the source or drain of the device is known as charge injection, and is denoted by the symbol Q_{INJ} . [Figure 23](#) shows the setup used to measure charge injection from source (Sx) to drain (D).

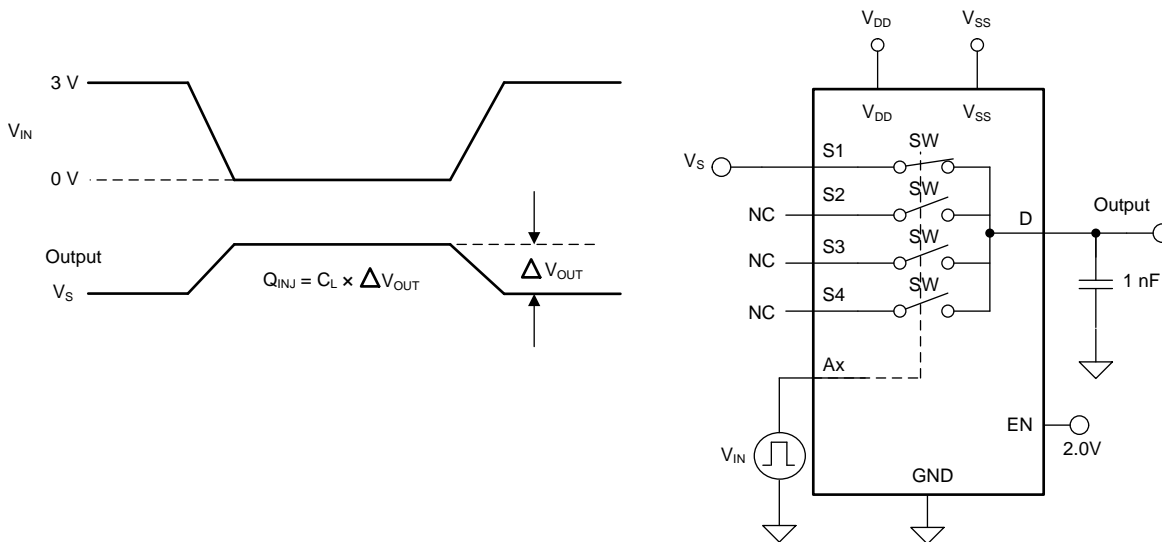


Figure 23. Charge-Injection Measurement Setup

8.1.8 Off Isolation

Off isolation is defined as the voltage at the drain pin (D) of the TMUX6104 when a 1- V_{RMS} signal is applied to the source pin (Sx) of an off-channel. [Figure 24](#) shows the setup used to measure off isolation. Use [Equation 2](#) to compute off isolation.

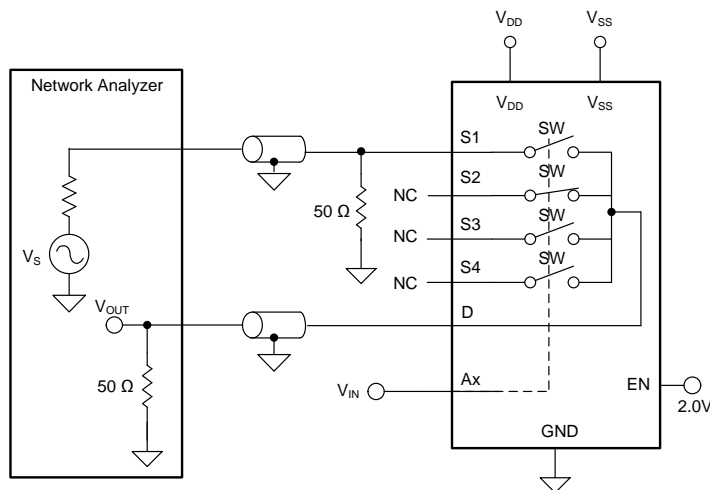


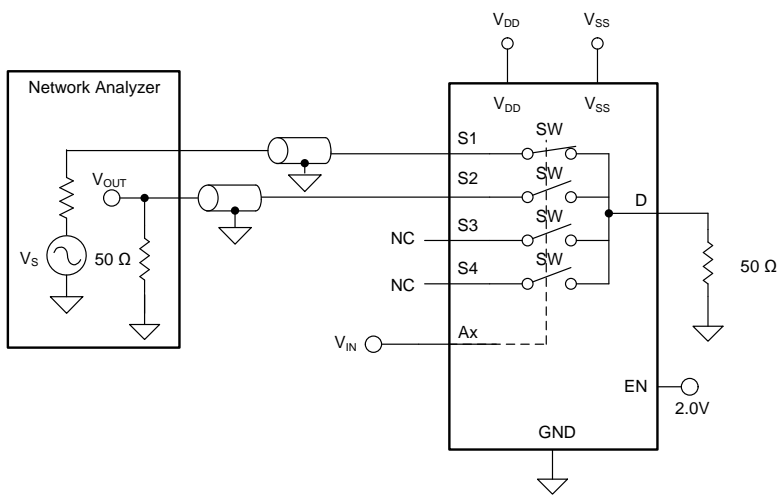
Figure 24. Off Isolation Measurement Setup

$$\text{Off Isolation} = 20 \cdot \text{Log} \left(\frac{V_{OUT}}{V_S} \right)$$

(2)

Overview (continued)

8.1.9 Channel-to-Channel Crosstalk

Channel-to-channel crosstalk is defined as the voltage at the source pin (Sx) of an off-channel, when a 1- V_{RMS} signal is applied at the source pin (Sx) of an on-channel.  shows the setup used to measure, and 式 3 is the equation used to compute, channel-to-channel crosstalk.

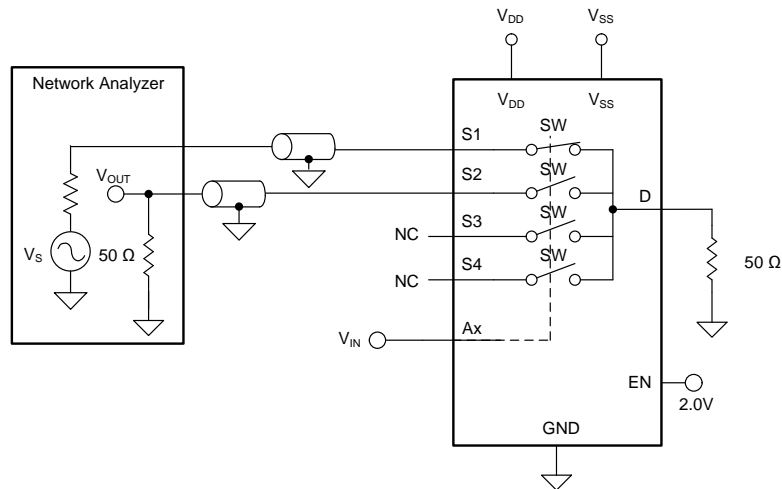
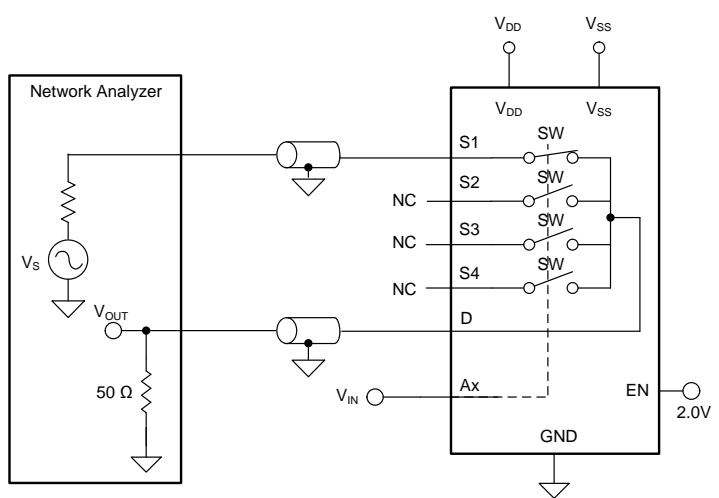


图 25. Channel-to-Channel Crosstalk Measurement Setup

$$\text{Channel-to-Channel Crosstalk} = 20 \cdot \text{Log} \left(\frac{V_{OUT}}{V_S} \right) \tag{3}$$

8.1.10 Bandwidth

Bandwidth is defined as the range of frequencies that are attenuated by < 3 dB when the input is applied to the source pin (Sx) of an on-channel, and the output is measured at the drain pin (D) of the TMUX6104.  shows the setup used to measure bandwidth of the mux. Use 式 4 to compute the attenuation.

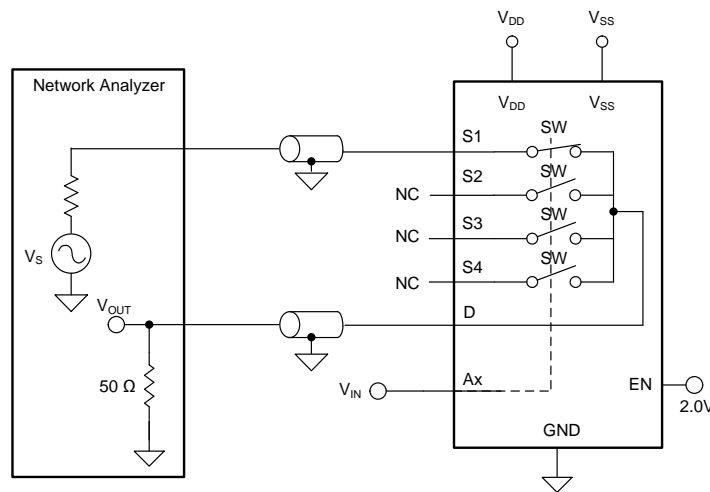


图 26. Bandwidth Measurement Setup

$$\text{Attenuation} = 20 \times \text{Log} \left(\frac{V_{OUT}}{V_S} \right) \tag{4}$$

Overview (continued)

8.1.11 THD + Noise

The total harmonic distortion (THD) of a signal is a measurement of the harmonic distortion, and is defined as the ratio of the sum of the powers of all harmonic components to the power of the fundamental frequency at the mux output. The on-resistance of the TMUX6104 varies with the amplitude of the input signal and results in distortion when the drain pin is connected to a low-impedance load. Total harmonic distortion plus noise is denoted as THD+N.

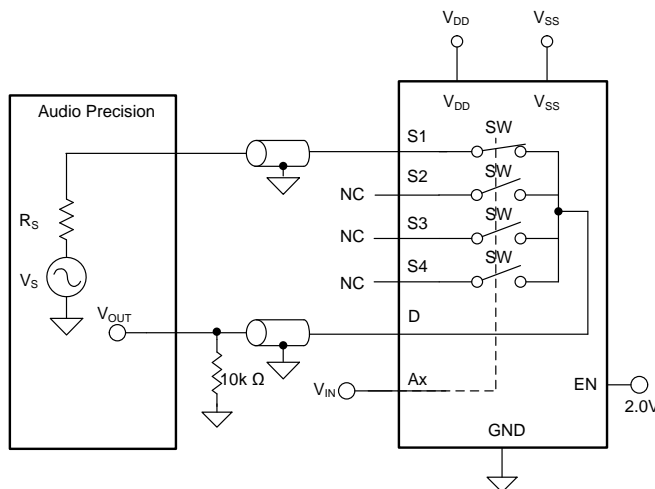


Figure 27. THD+N Measurement Setup

8.1.12 AC Power Supply Rejection Ratio (AC PSRR)

AC PSRR measures the ability of a device to prevent noise and spurious signals that appear on the supply voltage pin from coupling to the output of the switch. The DC voltage on the device supply is modulated by a sine wave of 620 mV_{PP}. The ratio of the amplitude of signal on the output to the amplitude of the modulated signal is the AC PSRR.

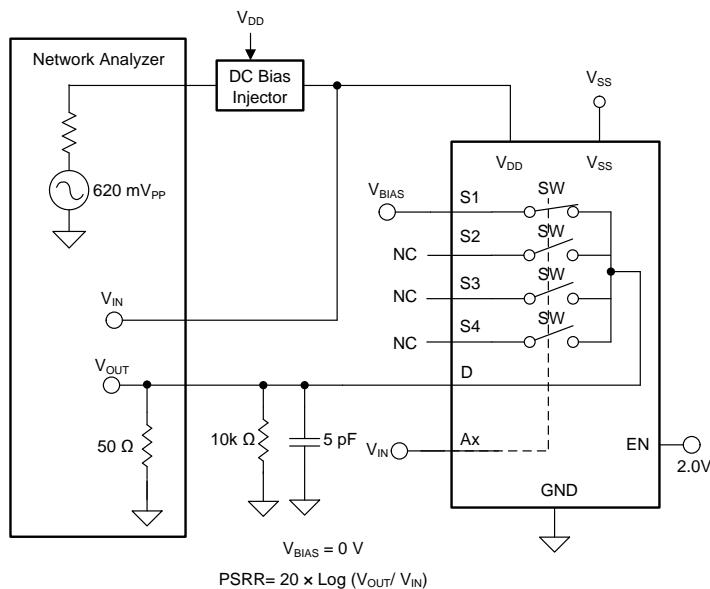
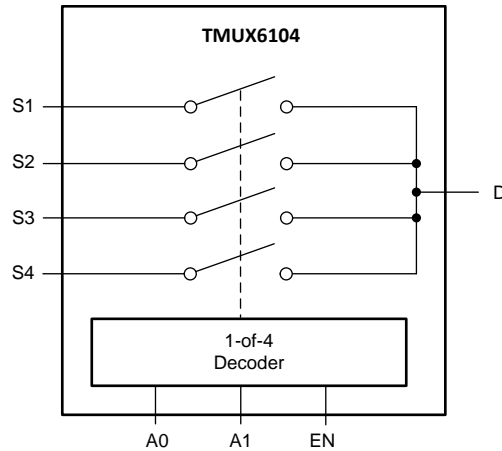


Figure 28. AC PSRR Measurement Setup

Overview (continued)

The [Functional Block Diagram](#) section provides a top-level block diagram of the TMUX6104. The TMUX6104 is a 4-channel, single-ended, analog multiplexer. Each channel is turned on or turned off based on the state of the address lines and enable pin.

8.2 Functional Block Diagram



Copyright © 2017, Texas Instruments Incorporated

8.3 Feature Description

8.3.1 Ultralow Leakage Current

The TMUX6104 provide extremely low on- and off-leakage currents. The TMUX6104 is capable of switching signals from high source-impedance inputs into a high input-impedance op amp with minimal offset error because of the ultralow leakage currents. [Figure 29](#) shows typical leakage currents of the TMUX6104 versus temperature.

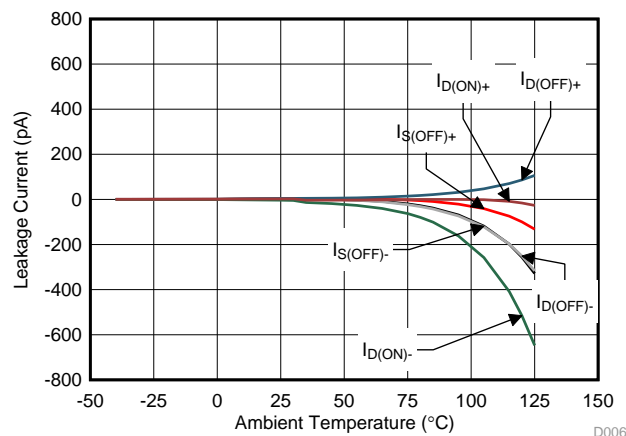


Figure 29. Leakage Current vs Temperature

8.3.2 Ultralow Charge Injection

The TMUX6104 is implemented with simple transmission gate topology, as shown in [Figure 30](#). Any mismatch in the stray capacitance associated with the NMOS and PMOS causes an output level change whenever the switch is opened or closed.

Feature Description (continued)

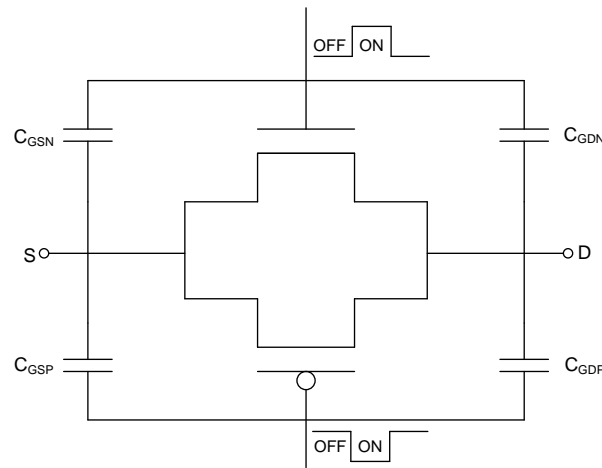


Figure 30. Transmission Gate Topology

The TMUX6119 utilizes special charge-injection cancellation circuitry that reduces the source (Sx) to drain (D) charge injection to as low as -0.35 pC at $V_S = 0$ V, and -0.41 pC in the full signal range, as shown in Figure 31.

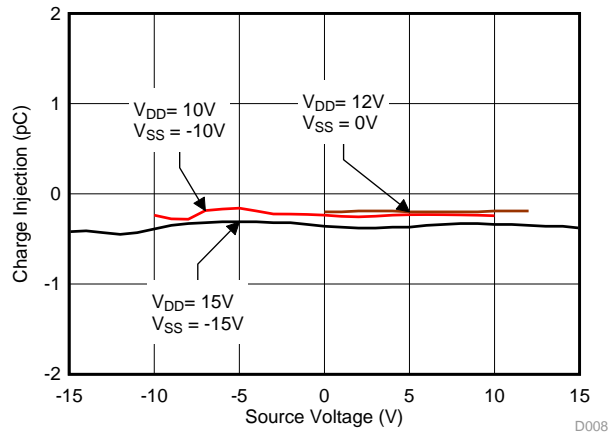
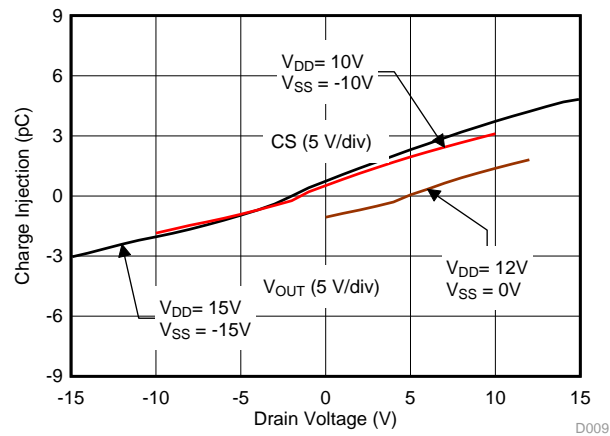


Figure 31. Source-to-Drain Charge Injection vs Source Voltage

The drain (D)-to-source (Sx) charge injection becomes important when the device is used as a demultiplexer (demux), where the drain (D) becomes the input and the source (Sx) becomes the output. Figure 32 shows the drain-to-source charge injection across the full signal range.

Feature Description (continued)

32. Drain-to-Source Charge Injection vs Drain Voltage
8.3.3 Bidirectional and Rail-to-Rail Operation

The TMUX6104 conducts equally well from source (Sx) to drain (D) or from drain (D) to source (Sx). Each TMUX6104 channel has very similar characteristics in both directions. The valid analog signal for TMUX6104 ranges from V_{SS} to V_{DD} . The input signal to the TMUX6104 swings from V_{SS} to V_{DD} without any significant degradation in performance.

8.4 Device Functional Modes

When the EN pin of the TMUX6104 is pulled high, one of the four switches is closed based on the state of the address pins (A0 and A1). When the EN pin is pulled low, all four switches remain open irrespective of the state of the address pins. The EN pin is weakly pull-down internally through a 6 M Ω resistor; thereby, setting each channel to the open state if the EN pin is not actively driven. The address pins are also weakly pulled-down through an internal 6 M Ω resistor, allowing channel 1 (S1 to D) to be selected by default when EN pin is driven high. Both the EN pin and the address pins can be connected to V_{DD} (as high as 16.5 V).

9 Application and Implementation

注

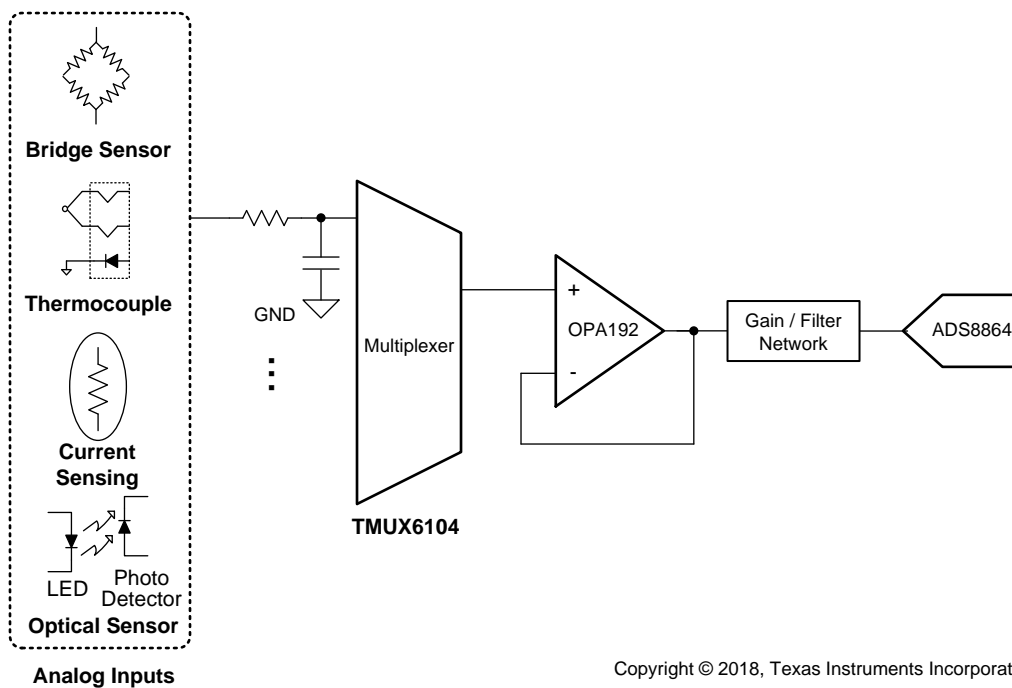
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TMUX6104 offers outstanding input/output leakage currents and ultralow charge injection. These devices operate up to 33 V, and offer true rail-to-rail input and output. The on-capacitance of the TMUX6104 is very low. These features makes the TMUX6104 a precision, robust, high-performance analog multiplexer for high-voltage, industrial applications.

9.2 Typical Application

Figure 33 shows a 16-bit, differential, 4-channel, multiplexed, data-acquisition system. This example is typical in industrial applications that require low distortion and a high-voltage input. The circuit uses the ADS8864, a 16-bit, 400-kSPS successive-approximation-resistor (SAR) analog-to-digital converter (ADC), along with a precision, high-voltage, signal-conditioning front end, and a 4-channel single-ended mux. This TI Precision Design details the process for optimizing the precision, high-voltage, front-end drive circuit using the TMUX6104 and OPA192 to achieve excellent dynamic performance and linearity with the ADS8864.



Copyright © 2018, Texas Instruments Incorporated

Figure 33. 16-Bit Precision Multiplexed Data-Acquisition System for High-Voltage Inputs With Lowest Distortion

Typical Application (continued)

9.2.1 Design Requirements

The primary objective is to design a ± 15 V, single-ended, 4-channel, multiplexed, data-acquisition system with lowest distortion using the 16-bit ADS8864 at a throughput of 400 kSPS for a 10-kHz, full-scale, pure, sine-wave input. The design requirements for this block design are:

- System supply voltage: ± 15 V
- ADC supply voltage: 3.3 V
- ADC sampling rate: 400 kSPS
- ADC reference voltage (REFP): 4.096 V
- System input signal: A high-voltage differential input signal with a peak amplitude of 15 V and frequency (f_{IN}) of 10 kHz are applied to each differential input of the mux.

9.2.2 Detailed Design Procedure

The purpose of this precision design is to design an optimal, high-voltage, multiplexed, data-acquisition system for highest system linearity and fast settling. The overall system block diagram is illustrated in [Figure 33](#). The circuit is a multichannel, data-acquisition signal chain consisting of an input low-pass filter, mux, mux output buffer, and attenuating SAR ADC driver. The architecture allows fast sampling of multiple channels using a single ADC, providing a low-cost solution. This design systematically approaches each analog circuit block to achieve a 16-bit settling for a full-scale input stage voltage and linearity for a 10-kHz sinusoidal input signal at each input channel.

9.2.3 Application Curve

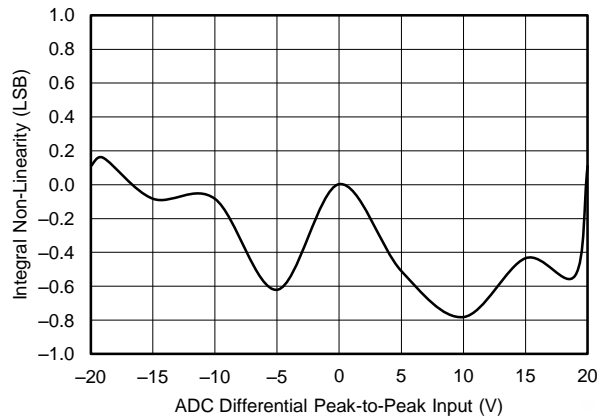


Figure 34. ADC 16-Bit Linearity Error for the Multiplexed Data-Acquisition Block

10 Power Supply Recommendations

The TMUX6104 operates across a wide supply range of $\pm 5\text{ V}$ to $\pm 16.5\text{ V}$ (10 V to 16.5 V in single-supply mode). The device also perform well with unsymmetric supplies such as $V_{DD} = 12\text{ V}$ and $V_{SS} = -5\text{ V}$. For reliable operation, use a supply decoupling capacitor ranging between $0.1\ \mu\text{F}$ to $10\ \mu\text{F}$ at both the V_{DD} and V_{SS} pins to ground.

The on-resistance of the TMUX6104 varies with supply voltage, as illustrated in [Figure 35](#)

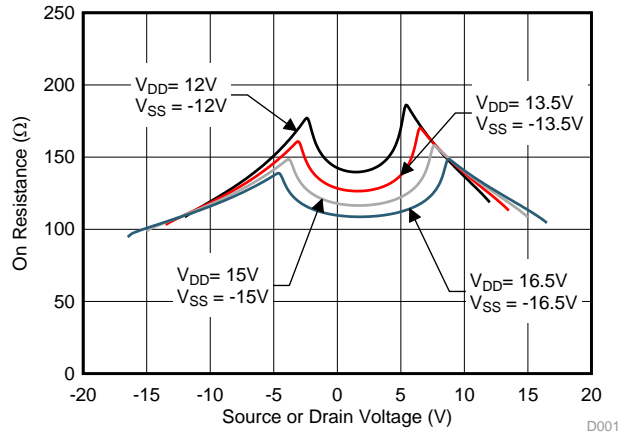


Figure 35. On-Resistance Variation With Supply and Input Voltage

11 Layout

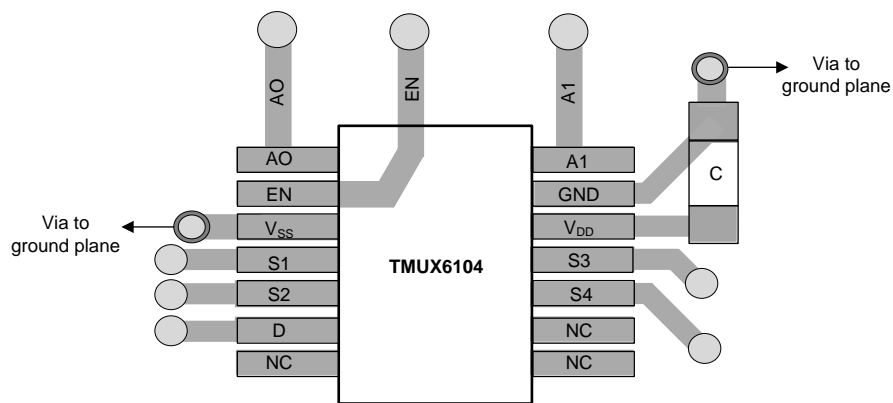
11.1 Layout Guidelines

☒ 36 illustrates an example of a PCB layout with the TMUX6104.

Some key considerations are:

1. Decouple the V_{DD} and V_{SS} pins with a 0.1- μF capacitor, placed as close to the pin as possible. Make sure that the capacitor voltage rating is sufficient for the V_{DD} and V_{SS} supplies.
2. Keep the input lines as short as possible.
3. Use a solid ground plane to help distribute heat and reduce electromagnetic interference (EMI) noise pickup.
4. Do not run sensitive analog traces in parallel with digital traces. Avoid crossing digital and analog traces if possible, and only make perpendicular crossings when necessary.

11.2 Layout Example



Copyright © 2018, Texas Instruments Incorporated

☒ 36. TMUX6104 Layout Example

12 デバイスおよびドキュメントのサポート

12.1 ドキュメントのサポート

12.1.1 関連資料

- 『[ADS8664 12ビット、500kSPS、4および8チャンネル、シングル電源、バイポーラ入力範囲のSAR ADC](#)』(SBAS492)
- 『[OPA192 36V、高精度、レール・ツー・レール入力/出力、低オフセット電圧、低入力バイアス電流、e-trim™搭載のオペアンプ](#)』(SBOS620)

12.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.comのデバイス製品フォルダを開いてください。右上の隅にある「通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

12.3 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™オンライン・コミュニティ *TIのE2E (Engineer-to-Engineer) コミュニティ*。エンジニア間の共同作業を促進するために開設されたものです。e2e.ti.comでは、他のエンジニアに質問し、知識を共有し、アイデアを検討して、問題解決に役立てることができます。

設計サポート *TIの設計サポート* 役に立つE2Eフォーラムや、設計サポート・ツールをすばやく見つけることができます。技術サポート用の連絡先情報も参照できます。

12.4 商標

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

12.5 静電気放電に関する注意事項



すべての集積回路は、適切なESD保護方法を用いて、取扱いと保存を行うようにして下さい。

静電気放電はわずかな性能の低下から完全なデバイスの故障に至るまで、様々な損傷を与えます。高精度の集積回路は、損傷に対して敏感であり、極めてわずかなパラメータの変化により、デバイスに規定された仕様に適合しなくなる場合があります。

12.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TMUX6104PWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	MUX6104	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

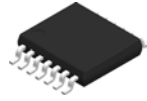
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TMUX6104PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TMUX6104PWR	TSSOP	PW	14	2000	356.0	356.0	35.0

PW0014A



PACKAGE OUTLINE

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



4220202/B 12/2023

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE STENCIL DESIGN

PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220202/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

重要なお知らせと免責事項

TI は、技術データと信頼性データ(データシートを含みます)、設計リソース(リファレンス・デザインを含みます)、アプリケーションや設計に関する各種アドバイス、Web ツール、安全性情報、その他のリソースを、欠陥が存在する可能性のある「現状のまま」提供しており、商品性および特定目的に対する適合性の黙示保証、第三者の知的財産権の非侵害保証を含むいかなる保証も、明示的または黙示的にかかわらず拒否します。

これらのリソースは、TI 製品を使用する設計の経験を積んだ開発者への提供を意図したものです。(1) お客様のアプリケーションに適した TI 製品の選定、(2) お客様のアプリケーションの設計、検証、試験、(3) お客様のアプリケーションに該当する各種規格や、その他のあらゆる安全性、セキュリティ、規制、または他の要件への確実な適合に関する責任を、お客様のみが単独で負うものとし、

上記の各種リソースは、予告なく変更される可能性があります。これらのリソースは、リソースで説明されている TI 製品を使用するアプリケーションの開発の目的でのみ、TI はその使用をお客様に許諾します。これらのリソースに関して、他の目的で複製することや掲載することは禁止されています。TI や第三者の知的財産権のライセンスが付与されている訳ではありません。お客様は、これらのリソースを自身で使用した結果発生するあらゆる申し立て、損害、費用、損失、責任について、TI およびその代理人を完全に補償するものとし、TI は一切の責任を拒否します。

TI の製品は、[TI の販売条件](#)、または [ti.com](#) やかかる TI 製品の関連資料などのいずれかを通じて提供する適用可能な条項の下で提供されています。TI がこれらのリソースを提供することは、適用される TI の保証または他の保証の放棄の拡大や変更を意味するものではありません。

お客様がいかなる追加条項または代替条項を提案した場合でも、TI はそれらに異議を唱え、拒否します。

郵送先住所 : Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2024, Texas Instruments Incorporated